

1.5W, 5kV_{RMS} Isolated DC-DC Converter with Integrated Transformer

1 Features

- Complete Switch Mode Power Supply
- High integration with internal transformer
- Soft-start reduces input inrush current and output overshoot
- Hiccup current-limit protection
- Thermal shutdown
- 4.5 V to 5.5 V Input Voltage Range
- Selectable Output voltages
- 3.3V and 5V output options
- 3.7V and 5.4V output options provide headroom voltage to power LDO
- Delivers up to 1.5W(5V/300mA) Typical Output Power
- Excellent Load Transient Response
- Complies with CISPR32 Class B Radiated Emissions
- Up to ±3kV HBM and ±2kV CDM ESD protection
- Robust Galvanic Isolation Barrier
- High lifetime: > 40 years
- Up to 5kV_{RMS} isolation rating
- ±150 kV/µs typical CMTI
- Wide Operating Temperature Range: -40°C to 125°C
- Low Profile SOIC16-WB (10.30mm × 7.50) Package
- Safety-Related Certifications (Pending)
 - VDE certification according to DIN EN IEC60747-17(VDE 0884-17):2021-10
 - UL certification according to UL1577
 - CQC certification according to GB4843.1-2022

2 Applications

- Tractor inverters
- Onboard chargers and DC/DC converters
- Battery management system
- Electric compressor

3 General Description

The CA-IS3115AW-Q1 is a family of complete isolated DC-DC converters with up to $5kV_{RMS}$ isolation rating. These devices integrate most of the components needed for an

isolated power supply —switching controller, power switches, transformer, soft-start, protection circuit etc. into a single, compact SOIC package. The result is an efficient and compact fully integrated solution that is easy to comply with EMI requirements and makes power-supply isolation design as easy as possible. Operating over an input voltage range of 4.5V to 5.5V, the CA-IS3115AW-Q1 devices provide a fixed output voltage of 3.3V, 3.7V, 5V or 5.4V set by pin SEL. 3.7V and 5.4V output options provide headroom voltage to power an LDO. Only output, input bypass capacitors, and a pull-up resistor for 3.7V or 5.4V outputs are needed to finish the design.

The CA-IS3115AW-Q1 devices feature a unique control scheme, which can quickly respond to load transient and accurately regulate the output voltage. The devices are capable of delivering a load up to 1.5W output power and offering soft-start, current limit, short-circuit protection and thermal shutdown protection features to better enhance the reliability of the system. The CA-IS3115AW-Q1 devices include an enable input pin (EN). Connect the EN pin to the VINP input voltage or force this pin high to turn on the DC-DC converter. Force this pin low to disable the device and enter shutdown mode. In shutdown mode, the device stops switching operation with microampere standby supply current.

The CA-IS3115AW-Q1 devices are available in wide-body SOIC16 package with creepage and clearance > 8mm, and operate over -40° C to $+125^{\circ}$ C temperature range.

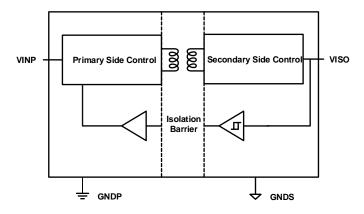
Device Information

| Part number | Package | Package size (NOM) |
|----------------|------------------|-----------------------|
| CA-IS3115AW-Q1 | SOIC16- WB(W) | 10.30 mm × 7.50 mm |



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4 Ordering Information

Table 4-1. Ordering Information

| Part # | Output Power (W) | Isolation Rating(kV _{RMS}) | Package |
|----------------|------------------|--------------------------------------|-----------|
| CA-IS3115AW-Q1 | 1.5 | 5.0 | SOIC16-WB |



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5 Revision history

| Revision Number | Description | Revised Date | Page Changed |
|------------------------|---|--------------|--------------|
| Preliminary Version | N/A | 2023/10/17 | N/A |
| Version 1.00 | Update isolation ratings | 2023/12/01 | 6,7 |
| Version 1.01 | Adds output derating curves | 2024/01/03 | 11,12 |
| Version 1.02 | Adds Short circuit protection function description | 2024/01/09 | 14 |
| Version 1.03 | Update VDE,UL,CQC,TUV information Update the test conditions of V _{IOSM} | 2024/04/16 | 1,6,7 |
| Version 1.04 | Update the test conditions of VISO _(LOAD) | 2024/05/14 | 8 |
| Version 1.05 | Add Capacitor value range in VISO pin in table of section 7.3 Update the Maximum Value of I _{VINP_SC} Update Figure 9-3. Recommended Bypass Capacitors Placement | 2024/06/19 | 5, 8,16 |



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6 Pin Configuration and Description

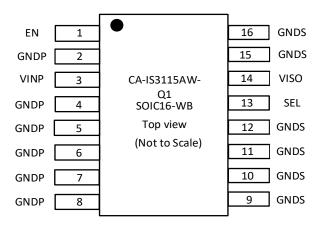


Figure 6-1. CA-IS3115AW-Q1 Top View

Table 6-1. CA-IS3115AW-Q1 Pin Description

| Pin name | Pin number | Туре | Description |
|----------|-----------------------|-------|---|
| EN | 1 | Input | Enable input, active-high. Force this pin high to enable the device. Force this pin low to disable the device and put the device into shutdown mode. |
| VINP | 3 | Power | Primary side supply input. Connect VINP to GNDP with both 0.1μ F and 10μ F capacitors as close to the device(pin 3 and pin 4) as possible. |
| GNDP | 2, 4, 5, 6, 7, 8 | GND | Primary side local ground. |
| GNDS | 9, 10, 11, 12, 15, 16 | GND | Secondary side ground return connection for V _{ISO} . |
| SEL | 13 | Input | Output voltage V _{ISO} select pin: $V_{ISO} = 5.0 V$ when SEL is shorted to VISO; $V_{ISO} = 5.4 V$ when SEL is connected to VISO through a 100k Ω resistor; $V_{ISO} = 3.3 V$ when SEL is shorted to GNDS; $V_{ISO} = 3.7V$ when SEL is connected to GNDS through a 100k Ω resistor. Don't leave SEL pin open. |
| VISO | 14 | Power | Isolated supply voltage pin. Connnect VISO to GNDS with both 0.1μ F and 10μ F capacitors as close to the device(pin 14 and pin 15) as possible. |



7 Specifications

7.1 Absolute Maximum Ratings^{1, 2}

| | Parameters | | Minimum value | Maximum value | Unit |
|---------------------|---|----------------------|------------------|------------------------------------|-------------|
| V _{INP} | Power supply voltage | | -0.5 | 6.0 | V |
| V _{ISO} | Isolated supply voltage | | -0.5 | 6.0 | V |
| EN | EN input voltage | | -0.5 | V _{INP} +0.3 ³ | V |
| SEL | SEL input voltage | | -0.5 | V _{ISO} +0.3 ³ | V |
| TJ | Junction temperature | | -40 | 150 | °C |
| T _{STG} | Storage temperature range | | -65 | 150 | °C |
| Notes: | | | | | |
| 1. The stresses lis | ted under "Absolute Maximum Ratings" are stress ratings onl | y, not for functiona | al operation con | dition. Exposure 1 | to absolute |

 The stresses listed under "Absolute Maximum Ratings" are stress ratings only, not for functional operation of maximum rating conditions for extended periods may cause permanent damage to the device.

- 2. All voltage values are with respect to the local ground (GNDP or GNDS) and are peak voltage values.
- 3. Maximum voltage must not be exceed 6 V.

7.2 ESD Ratings

| | | | Value | Unit |
|------------------|---|--|-------|------|
| V _{ESD} | Electrostatic discharge | Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins ¹ | ±3000 | V |
| ▼ ESD | Liectiostatic discillarge | Charged device model (CDM), per JEDEC Specification JESD22-C101, all pins ² | ±2000 | v |
| Not | es: | | | |
| 1. | Per JEDEC document JEP155 | , 500V HBM allows safe manufacturing of standard ESD control process. | | |
| 2. | 2. Per JEDEC document JEP157, 250V CDM allows safe manufacturing of standard ESD control process. | | | |

7.3 Recommended Operating Conditions

| | Parameters | Minimum value | Typical value | Maximum value | Unit |
|-------------------|-----------------------------------|------------------|------------------|------------------|------|
| V _{INP} | Power supply voltage | 4.5 | 5 | 5.5 | V |
| V _{EN} | EN input voltage | 0 | | 5.5 | V |
| V _{ISO} | Isolated supply voltage | 0 | | 5.7 | V |
| V _{SEL} | SEL input voltage | 0 | | 5.7 | V |
| C _{VISO} | Capacitor value range in VISO pin | 4.7 | 10 | 1000 | μF |
| T _A | Ambient Temperature | -40 | | 125 | °C |
| Tj | Junction temperature | -40 | | 150 | °C |

7.4 Thermal Information

| | Thermal Metric | CA-IS3115AW-Q1 | 11 |
|------------------|--|----------------|------|
| | Thermal Metric | SOIC16-WB(W) | Unit |
| R _{0JA} | Junction-to-ambient thermal resistance | 68 | °C/W |
| R _{θJC} | Junction-to-case thermal resistance | 18 | |

7.5 Power Ratings

| | Parameters | Test Conditions | Minimum value | Typical value | Maximum value | Unit |
|----|-------------------|--|------------------|------------------|------------------|------|
| PD | Power dissipation | V_{INP} = 5.5V, V_{ISO} = 5.4V, 300mA output current | | | 3 | W |

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7.6 Insulation Specifications

| | Parameters | Test Conditions | Value | Uni |
|------------------------|---|--|-------------------|-----------------|
| CLR | External clearance | Shortest terminal-to-terminal distance through air | 8 | mm |
| CPG | External creepage | Shortest terminal-to-terminal distance across the package surface | 8 | mm |
| DTI | Distance through the insulation | Minimum internal gap (internal clearance) | 28 | μn |
| CTI | Comparative tracking index | DIN EN 60112 (VDE 0303-11); IEC 60112 | >600 | V |
| | Material group | According to IEC 60664-1 | I | |
| | | Rated mains voltage ≤ 300 V _{RMS} | I-IV | |
| | IEC 60664-1 over-voltage category | Rated mains voltage ≤ 600 V _{RMS} | I-IV | |
| | | Rated mains voltage ≤ 1000 V _{RMS} | 1-111 | |
| DIN V V | VDE V 0884-17:2021-10 ¹ | · · · · | | |
| V _{IORM} | Maximum repetitive peak isolation voltage | AC voltage (bipolar) | 2121 | VP |
| V _{IOWM} | Maximum operating isolation voltage | AC voltage; time-dependent dielectric breakdown (TDDB) test | 1500 | V _{RI} |
| | | DC voltage | 2121 | VD |
| V _{IOTM} | Maximum transient isolation voltage | $V_{TEST} = V_{IOTM}$, t=60 s (qualification); $V_{TEST} = 1.2 \times V_{IOTM}$, t=1 s (100% product test) | 7070 | V _P |
| V _{IOSM} | Maximum surge isolation voltage ² | Test method per IEC 62368-1, 1.2/50 μ s waveform, V _{TEST} = 1.6 × V _{IOSM} (qualification) | 8000 | V |
| | | Method a, after input/output safety tests subgroup 2/3, $V_{ini} = V_{IOTM}$, $t_{ini} = 60s$; $V_{pd(m)} = 1.2 \times V_{IORM}$, $t_m = 10s$ | ≤5 | |
| q _{pd} | Apparent charge ³ | Method a, after environmental tests subgroup 1, $V_{ini} = V_{IOTM}$, $t_{ini} = 60s$; $V_{pd(m)} = 1.6 \times V_{IORM}$, $t_m = 10s$ | ≤5 | p(|
| | | | ≤5 | |
| CIO | Barrier capacitance, input to output ⁴ | $V_{IO} = 0.4 \times \sin(2\pi ft), f = 1 \text{ MHz}$ | 3.5 | pF |
| | | V _{IO} = 500 V, T _A = 25°C | >10 ¹² | |
| R _{IO} | Isolation resistance , input to output ⁴ | $V_{IO} = 500 \text{ V}, 100^{\circ}\text{C} \le T_{A} \le 125^{\circ}\text{C}$ | >1011 | Ω |
| | | $V_{IO} = 500 \text{ V at } T_{S} = 150^{\circ}\text{C}$ | >109 | |
| | Pollution degree | | 2 | |
| UL 157 | 7 | | | |
| V _{ISO} | Maximum isolation voltage | $V_{\text{TEST}} = V_{\text{ISO}}$, t = 60 s (certified) $V_{\text{TEST}} = 1.2 \times V_{\text{ISO}}$, t = 1 s (100% production test) | 5000 | V _{RI} |

2. Devices are immersed in oil during surge characterization.

3. The characterization charge is discharging charge (pd) caused by partial discharge.

4. Capacitance and resistance are measured with all pins on field-side and logic-side tied together.



7.7 Safety-Related Certifications

| VDE | UL | CQC |
|---|--|--------------------------------------|
| Certified according to DIN V VDE V 0884- | Certified according to UL 1577 | Certified according to GB4943.1-2011 |
| 17:2021-10 | Component Recognition Program | |
| Maximum transient isolation voltage: 7070 V _{PK} | Maximum isolation voltage: 5000 V _{RMS} | reinforced isolation |
| Maximum repetitive peak isolation voltage: | | (Altitude≤5000m) |
| 2121 V _{PK} | | |
| Maximum surge isolation voltage: 8000 V_{PK} | | |
| Certificate number: 40057278 (reinforced | Certificate number: E511334 | Certification number: CQC23001406424 |
| isolation) | | |

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7.8 Electrical Characteristics

Over operating temperature range $T_A = -40$ to 125°C, $V_{INP} = 4.5V$ to 5.5V, SEL connected to V_{ISO} , $C_{VINP} = C_{VISO} = 10\mu$ F, unless otherwise specified. All typical specs are at $T_A = 25$ °C and $V_{INP} = 5V$.

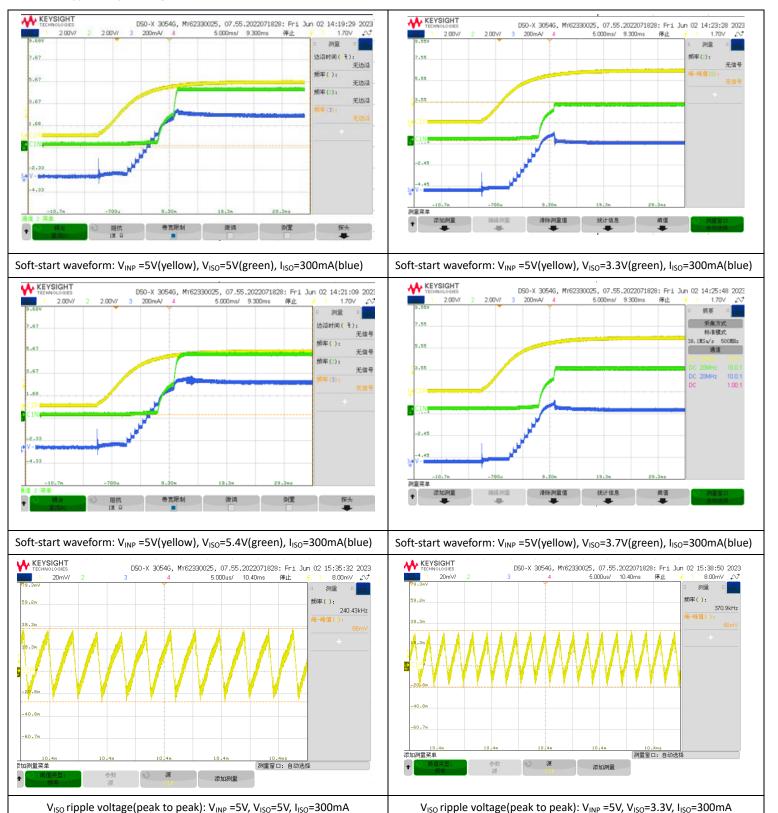
| | Parameters | Test Conditions | Minimum value | ТҮР | Maximum value | Unit | |
|-------------------------|---|---|------------------|------|------------------|------|--|
| Power Sup | oply Input | · | | | | | |
| IVINP_SD VINP | shutdown current | EN = LOW | | 0.5 | 30 | μΑ | |
| | | EN = HIGH, SEL connected to V_{ISO} (5V output) | | 4.9 | 20 | mA | |
| I _{VINP_O} | V _{INP} quiescent current | EN = HIGH, SEL 100k Ω to VISO (5.4Voutput) | | 5.2 | 20 | mA | |
| | I _{OUT} = 0% load | EN = HIGH, SEL connected to GNDS (3.3V output) | | 4.1 | 20 | mA | |
| | | EN = HIGH, SEL 100k Ω to GNDS (3.7V output) | | 4.3 | 20 | mA | |
| I _{VINP_SC} | DC current from VINP supply under short circuit on VISO | VISO short to GNDS | | 77 | 125 | mA | |
| V _{UVLO+} | Input undervoltage lockout rising threshold | | | 2.7 | 3 | v | |
| V _{UVLO-} | Input undervoltage lockout falling threshold | | 2.1 | 2.3 | | v | |
| V _{HYS(UVLO)} | Input undervoltage lockout hysteresis | | | 0.4 | 0.6 | V | |
| EN, SEL piı | ns | | | | | | |
| VIH_EN | EN Input threshold, logic HIGH | | $0.7V_{INP}$ | | | V | |
| VIL_EN | EN Input threshold, logic LOW | | | | 0.3VINP | V | |
| I _{EN} | Input leakage current | $V_{INP} = 5V, V_{EN} = 5V$ | | 10 | 20 | μA | |
| Isolated D | C-DC Converter | | | | | | |
| | | SEL connected to V_{ISO} (5V output), I_{ISO} = 150mA | 4.75 | 5.0 | 5.25 | - V | |
| | Isolated output voltage | SEL 100KΩ to VISO (5.4V output), I _{ISO} = 150mA | 5.13 | 5.4 | 5.67 | | |
| Viso | | SEL connected to GNDS (3.3V output), I _{ISO} = 200mA | 3.13 | 3.3 | 3.47 | | |
| | | SEL 100K Ω to GNDS (3.7V output), I _{ISO} = 200mA | 3.51 | 3.7 | 3.89 | | |
| | | SEL connected to V _{ISO} (5V output) | 240 | 300 | | | |
| | | SEL 100KΩ to VISO (5.4V output) | 240 | 300 | | mA | |
| LOAD_MAX | Maximum load currrent | SEL connected to GNDS (3.3V output) | 320 | 400 | | | |
| | | SEL 100KΩ to GNDS (3.7V output) | 320 | 400 | | | |
| VISO(RIP) | Voltage ripple on isolated supply output (pk-pk) | 20MHz bandwidth, SEL short to VISO (5V input, 5V or 5.4V output),I _{ISO} = 150mA | | 65 | | | |
| | | 20MHz bandwidth, SEL short to GNDS (5V input, 3.3V or 3.7V output), I_{ISO} = 200mA | | 55 | | mV | |
| VISO | Line regulation | SEL short to VISO (5V or 5.4V output), I_{ISO} = 150mA, V_{INP} = 4.5V to 5.5 V | | 4 | 20 | mV/v | |
| VISO _(LINE) | | SEL short to GNDS (3.3V or 3.7V output), I_{ISO} = 200mA, V_{INP} = 4.5V to 5.5V | | 4 | 20 | mv/v | |
| VISO. | Load regulation | SEL short to VISO (5V input, 5V or 5.4V output), $I_{ISO} = 0$ to 240mA | | 0.5% | 2% | | |
| VISO _(LOAD) | Load regulation | SEL short to GNDS (5V input, 3.3V or 3.7V output), $I_{ISO} = 0$ to 320mA | | 0.5% | 2% | | |
| | Efficiency@movimum.load.com | I _{ISO} = 300 mA, C _{LOAD} = 0.1μF 10μF; V _{ISO} =5V, 5.4V | | 60% | | | |
| EFF | Efficiency@maximum load current | $I_{ISO} = 300$ mA, $C_{LOAD} = 0.1 \mu$ F 10μ F; $V_{ISO} = 3.3 V, 3.7 V$ | | 50% | | | |
| СМТІ | Common-mode transient immunity | Slew Rate of GNDP versus GNDS, V_{CM} =1200 V_{RMS} | ±150 | | | kV/μ | |
| t _{RISE} | V _{ISO} rise time | 10% to 90%, V _{ISO} =3.3V, 3.7V, 5.0V, 5.4V | 1 | | | ms | |
| V _{ISO} ripple | voltage (peak to peak) | 10% to 90% load step with 10mA/ μ s slew-rate; V _{ISO} | | 100 | | mV | |
| Viso load tr | ransient response | ripple voltage difference at two loads | | 5 | | μs | |

7.9 **MSL**

| Parameters | Standard | Level |
|------------|------------------------|-------|
| MSL | IPC/JEDEC J-STD-020D.1 | MSL 3 |



7.10 **Typical Operating Characteristics**





8.00mV 0.5

测量

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D50-X 3054G, MY62330025, 07.55.2022071828: Fri Jun 02 16:17:18 2023

停止

5.000us/ 10.39ms

CA-IS3115AW-Q1 Version1.05, 2024/6/19

DSO-X 3054G, MY62330025, 07.55.2022071828: Fri Jun 02 15:40:44 2023

停止

8.00mV 📣

5.000us/ 10.40ms

9.2

40.4

60.7m

添加测量菜单

Vout(V)

5.50

5 30 5.10

4.90 4.70

4.50 4.30

3.70

3.50

3.30 3.10

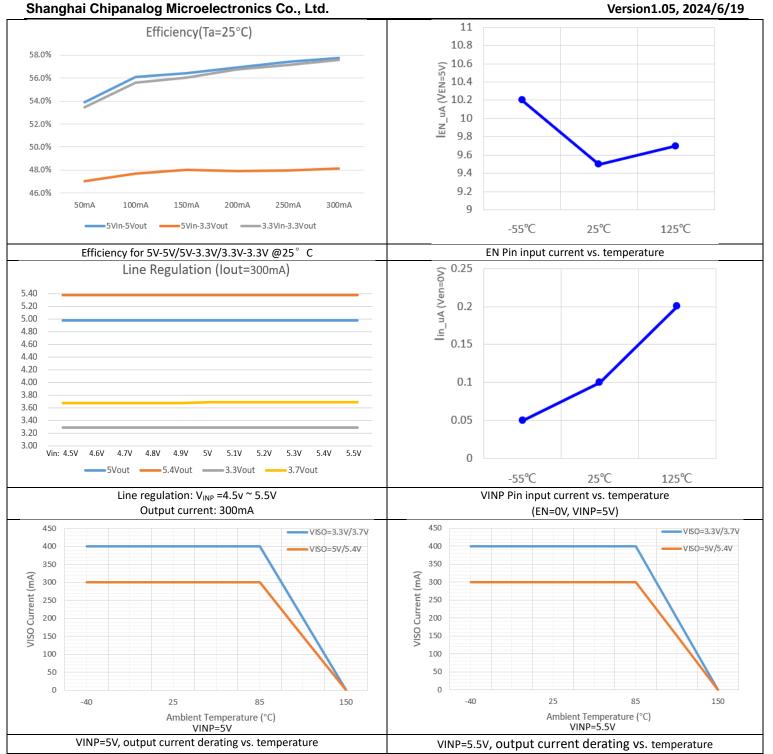
+

20mV/

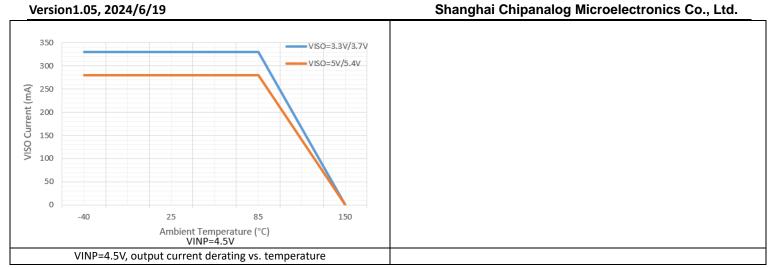
测量 频率(): 9.20 频率(1): 307.2kHz 345.8kHz 9.38 40.8 60.7 保存菜单 回调菜单 电子邮件 测量窗口: 自动选择 缺省/擦除 按下保存 源 添加测量 V_{ISO} ripple voltage(peak to peak): V_{INP} =5V, V_{ISO}=3.7V, I_{ISO}=300mA V_{ISO} ripple voltage(peak to peak): V_{INP} =5V, V_{ISO}=5.4V, I_{ISO}=300mA DS0-X 3054G, MY62330025, 07.55.2022071828: Thu Jun 08 14:50:30 2023 D90-X 3054G, MY62330025, 07.55.2022071828: Thu Jun 08 14:56:26 2023 50mV/ 153mA 📣 100mA/ 200.0us/ -2.000us 停止 153mA 50mV/ 100mA/ 200.0us/ -12.00us 停止 测量 测量 频率(1): 频率(<mark>1</mark>): 999.76Hz 1.0014kHz 峰-峰值(1): 峰-峰值(1): diki marmanahi lahan 98m\ 88m' lum dan pantanina mening 56.8m -4020 -2.000 398u 带宽限制 阻抗 1M Ω 微调 到置 带宽限制 阻抗 1¶ΓΩ 微调 倒置 探头 V_{ISO} Load transient response: $V_{INP} = 5V$, $V_{ISO} = 5V$ V_{ISO} Load transient response: V_{INP} =5V, V_{ISO}=3.3V Load-current: 30mA/270mA Load-current: 30mA/270mA Efficiency 70% Load Rugulation (Vin=5V) 65% 60% 55% 50% 45% VISO=5.0V 40% VISO=5.4V VISO=3.3V 35% 0mA 50mA 100mA 150mA 200mA 25mA 300mA VISO=3.7V VISO=5V VISO=5.4V VISO=3.3V VISO=3.7V 30% -55 5 25 45 85 105 125 -35 -15 65 Ta (°C) V_{ISO} load regulation: V_{INP} =5V, V_{ISO}=5V/5.4V/3.3V/3.7V Power supply efficiency vs. temperature Output current: 0mA-300mA V_{INP} =5V, V_{ISO}=5V/5.4V/3.3V/3.7V, output current = 300mA

20mV/











8 Detailed Description

8.1 Overview

The CA-IS3115AW-Q1 is a family of complete isolated DC-DC converters designed to provide isolated power with up to 1.5W output power across a $5kV_{RMS}$ isolation barrier. The devices operate over 4.5V to 5.5V input voltage range and use a proprietary control mechanism. The input supply V_{INP} is provided to the primary power controller that switches the power stage connected to the integrated transformer. Power is transferred to the secondary side and regulated to a fixed output voltage set by the SEL pin. The soft-start feature allows to reduce input inrush current and avoid output overshoot. These devices also incorporate an output enable (EN) control and undervoltage lockout(UVLO) function that allows the user to turn on the part at the desired input-voltage level. Figure 8-1 shows the CA-IS3115AW-Q1's functional block diagram. Connect the EN pin to VINP or force this pin high to turn on the DC-DC converter. Force this pin low to disable the device and enter low-current shutdown mode. These devices offer a ready-made, reliable, easy-to-use solution and allow users save PCB space and reduce design time for the popular 5V, 3.3V power supply systems.

These devices are provided with a robust overcurrent protection scheme that protects the devices under overload and output short-circuit conditions. A cycle-by-cycle peak current limit turns off the switching operation and triggers hiccup mode. Once the hiccup timeout period expires, soft-start is attempted again. Hiccup mode operation ensures low power dissipation under output short-circuit conditions.

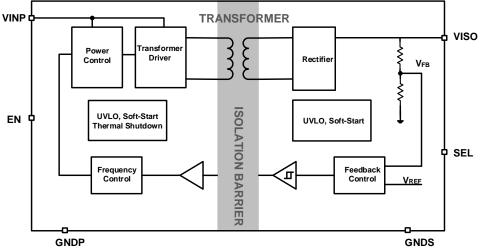


Figure 8-1. Functional Block Diagrams

8.2 Output Voltage Selection

At startup, the CA-IS3115AW-Q1 monitors the state of pin SEL after applying V_{INP} supply voltage above the UVLO rising threshold or enabling via the EN pin, to build the desired regulation voltage level for the V_{ISO} output. See Table 8-1 for the output voltage selection.

| EN | SEL | VISO |
|--------------------------------|-----------------|-------------|
| High | Sorted to VISO | 5V |
| High | 100kΩ to VISO | 5.4V |
| High | Shorted to GNDS | 3.3V |
| High | 100KΩ to GNDS | 3.7V |
| High | OPEN | Unsupported |
| Low | Х | 0V |
| Note: Don't leave SEL nin open | | |

Table 8-1. VISO Output Voltage Selection



CA-IS3115AW-Q1 Version1.05, 2024/6/19

8.3 Protection Functions

8.3.1 UVLO and Soft-Start

The CA-IS3115AW-Q1 undervoltage lockout (UVLO) on both V_{INP} power supply and V_{ISO} isolated supply. Upon power-up, the primary side transformer driver is disabled while the V_{INP} voltage is below the threshold voltage $V_{UVLO+}(2.7V, typ.)$, and V_{ISO} output is off. The output powers up once the threshold is met. This allows the user to turn on the part at stable input-voltage level.

For many applications, it is necessary to minimize the inrush current at start-up. The CA-IS3115AW-Q1 devices built-in soft-start circuit significantly reduces the start-up current spike and output voltage overshoot. Once input power supply is applied at VINP pin, the internal soft-start circuit will control the power delivered to the output gradually increase, allowing for a graceful turn-on ramp.

8.3.2 Current-limit Protection

The CA-IS3115AW-Q1 devices are provided with an over-current protection scheme that protects the device under overload and output short-circuit conditions. A cycle-by-cycle peak current limit turns off the switching operation and triggers a hiccup mode whenever the switch current exceeds the internal current limit. Once the hiccup timeout period expires, soft-start is attempted again. The hiccup condition is cleared when the over-current is removed.

8.3.3 Thermal Shutdown

Thermal-shutdown protection limits total power dissipation in the device. When the junction temperature of the device exceeds $175^{\circ}C(T_{SD})$, an on-chip thermal sensor shuts down the device, allowing the device to cool. The thermal sensor turns the device on again after the junction temperature cools and junction temperature drops to normal operation temperature range (< $150^{\circ}C$) of the device.



9 Applications Information

9.1 Typical Application Circuit

The CA-IS3115AW-Q1 devices are high-integration isolated power supply solution. Included in the package are the switching controller, power switches, transformer, and all support components. Only output and input bypass capacitors are needed to finish the design. For the applications with LDO post regulator, it needs a single $100k\Omega$ external resistor to set the output level to 3.7V or 5.4V, see Figure 9-1 typical application circuit.

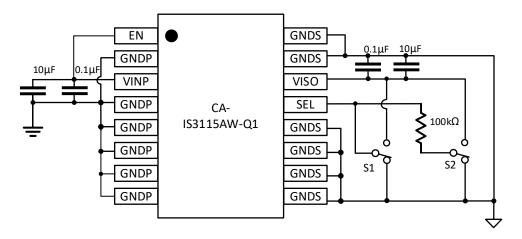


Figure 9-1. CA-IS3115AW-Q1 Typical Application Circuit

9.2 Input and Output Capacitors

The input capacitors (between VINP and GNDP) are required to reduce the peak current drawn from input power source and reduce the switching noise, increase efficiency. For the input capacitors, choose the ceramic capacitor because they have the lowest equivalent series resistance (ESR), smallest size, and lowest cost. For most applications, we recommend to use at least 0.1μ F and 10μ F ceramic capacitors with X5R or X7R temperature characteristic.

The output capacitors between VISO and GNDS are required as well to keep the output voltage ripple small and to ensure loop stability. These bypass capacitors must have low impedance at the switching frequency. Ceramic capacitors are recommended due to their small size and low ESR. Make sure the capacitors do not degrade their capacitance significantly over temperature and DC bias. It is recommended to have at least 10µF of effective capacitance at output.

9.3 PCB Layout Guidelines

High switching frequencies and large peak currents make PCB layout a very important part of the isolated DC-DC converter design. Good PCB design minimizes excessive electromagnetic interference (EMI) and voltage gradients in the ground plane to avoid instability and regulation errors. Even with the high level of integration, like CA-IS3115AW-Q1, users may fail to achieve specified operation with a haphazard or poor layout. So careful PCB layout is critical to achieve clean and stable operation, and ensure that the grounding and heat sinking are acceptable.

Place the input capacitors, output capacitors, and the CA-IS3115AW-Q1 IC on the same PCB layer. Place decoupling capacitors as close as possible to the CA-IS3115AW-Q1 device pins, see Figure 9-2 recommended components placement for the PCB layout. The paths must be wide and short to minimize inductance, also any via holes must be avoided on these paths. Connect all of the ground (GNDP, GNDS) connections to as large a plane area as possible for best heat-sinking. To ensure isolation performance between the primary side and secondary side, on the top layer and bottom layer keep the space under the CA-IS3115AW-Q1 device free from traces, vias, and pads to maintain maximum creepage distance (\geq 8mm).



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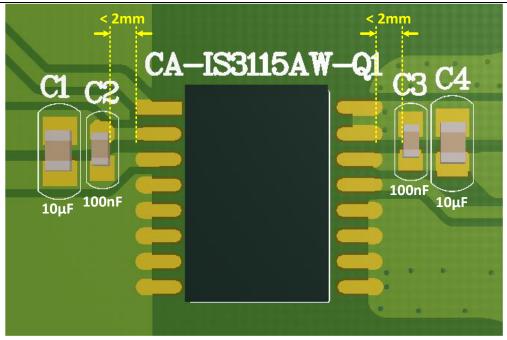
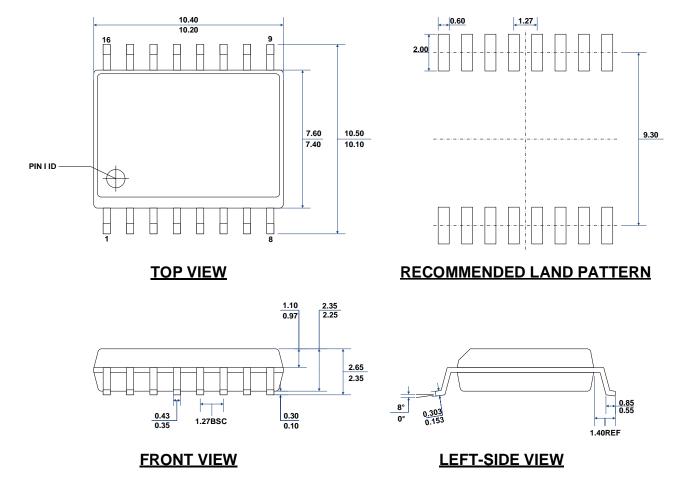


Figure 9-2. Recommended Bypass Capacitors Placement



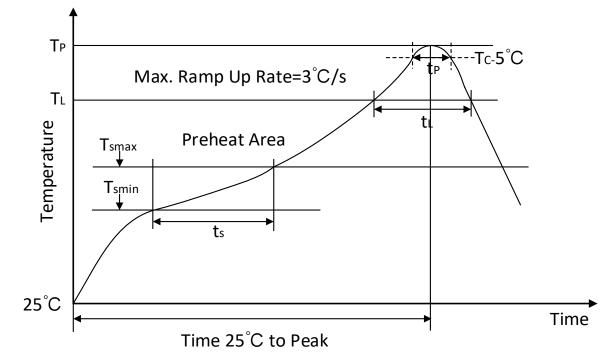
10 Package Information

The following figure illustrates the size drawing and recommended pad size of SOIC16-WB wide-body package for the CA-IS3115AW-Q1 isolated DC-DC converter. All dimensions are in millimeters.





11 Soldering Temperature (reflow) Profile



| Table 11-1. Soldering | Temperature | Parameter |
|-----------------------|-------------|-----------|
|-----------------------|-------------|-----------|

| Profile Feature | Pb-Free Assembly |
|--|------------------|
| Average ramp-up rate(217 °C to Peak) | 3°C /second max |
| Time of Preheat temp(from 150°C to 200°C | 60-120 second |
| Time to be maintained above 217°C | 60-150 second |
| Peak temperature | 260 +5/-0 °C |
| Time within 5°C of actual peak temp | 30 second |
| Ramp-down rate | 6°C /second max. |
| Time from 25°C to peak temp | 8 minutes max |

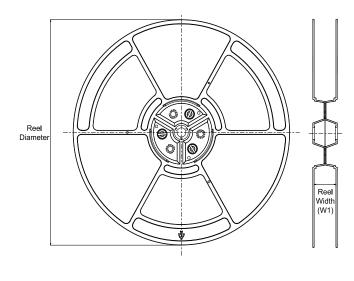


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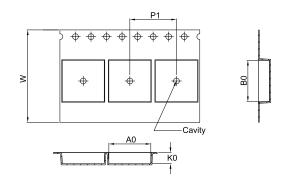
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Tape and Reel Information

REEL DIMENSIONS

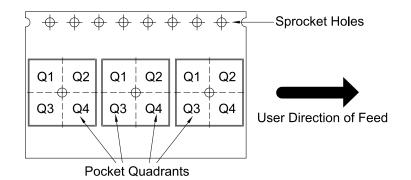


TAPE DIMENSIONS



| A0 | Dimension designed to accommodate the component width |
|----|---|
| B0 | Dimension designed to accommodate the component length |
| К0 | Dimension designed to accommodate the component thickness |
| W | Overall width of the carrier tape |
| P1 | Pitch between successive cavity centers |

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

| Device | Package Type | Package Drawing | Pins | SPQ | Reel Diameter (mm) | Reel Width W1 (mm) | A0 (mm) | B0 (mm) | K0 (mm) | P1 (mm) | W (mm) | Pin1 Quadrant |
|--------------------|-----------------|--------------------|------|------|--------------------------|-----------------------|------------|------------|------------|------------|-----------|------------------|
| CA-IS3115AW- Q1 | SOIC | W | 16 | 1000 | 330 | 16.4 | 10.8 | 10.7 | 2.9 | 12.0 | 24.0 | Q1 |



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